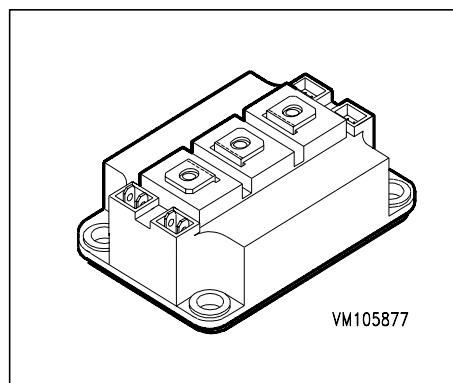


### IGBT Power Module

- Half-bridge
- Including fast free-wheeling diodes
- Package with insulated metal base plate



| Type               | $V_{CE}$ | $I_C$ | Package       | Ordering Code    |
|--------------------|----------|-------|---------------|------------------|
| BSM 100 GB 120 DN2 | 1200V    | 150A  | HALF-BRIDGE 2 | C67076-A2107-A70 |

### Maximum Ratings

| Parameter                                     | Symbol      | Values        | Unit               |
|-----------------------------------------------|-------------|---------------|--------------------|
| Collector-emitter voltage                     | $V_{CE}$    | 1200          | V                  |
| Collector-gate voltage                        | $V_{CGR}$   |               |                    |
| $R_{GE} = 20\text{ k}\Omega$                  |             | 1200          |                    |
| Gate-emitter voltage                          | $V_{GE}$    | $\pm 20$      |                    |
| DC collector current                          | $I_C$       |               | A                  |
| $T_C = 25\text{ }^{\circ}\text{C}$            |             | 150           |                    |
| $T_C = 80\text{ }^{\circ}\text{C}$            |             | 100           |                    |
| Pulsed collector current, $t_p = 1\text{ ms}$ | $I_{Cpuls}$ |               |                    |
| $T_C = 25\text{ }^{\circ}\text{C}$            |             | 300           |                    |
| $T_C = 80\text{ }^{\circ}\text{C}$            |             | 200           |                    |
| Power dissipation per IGBT                    | $P_{tot}$   |               | W                  |
| $T_C = 25\text{ }^{\circ}\text{C}$            |             | 800           |                    |
| Chip temperature                              | $T_j$       | + 150         | $^{\circ}\text{C}$ |
| Storage temperature                           | $T_{stg}$   | -55 ... + 150 |                    |
| Thermal resistance, chip case                 | $R_{thJC}$  | $\leq 0.16$   | K/W                |
| Diode thermal resistance, chip case           | $R_{thJCD}$ | $\leq 0.3$    |                    |
| Insulation test voltage, $t = 1\text{min.}$   | $V_{is}$    | 2500          | Vac                |
| Creepage distance                             | -           | 20            | mm                 |
| Clearance                                     | -           | 11            |                    |
| DIN humidity category, DIN 40 040             | -           | F             | -                  |
| IEC climatic category, DIN IEC 68-1           | -           | 55 / 150 / 56 |                    |

### Electrical Characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

| Parameter | Symbol | Values |      |      | Unit |
|-----------|--------|--------|------|------|------|
|           |        | min.   | typ. | max. |      |

#### Static Characteristics

|                                                                                                                                                                                |               |        |            |          |    |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------|--------|------------|----------|----|
| Gate threshold voltage<br>$V_{GE} = V_{CE}, I_C = 4\text{ mA}$                                                                                                                 | $V_{GE(th)}$  | 4.5    | 5.5        | 6.5      | V  |
| Collector-emitter saturation voltage<br>$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_j = 25\text{ °C}$<br>$V_{GE} = 15\text{ V}, I_C = 100\text{ A}, T_j = 125\text{ °C}$      | $V_{CE(sat)}$ | -<br>- | 2.5<br>3.1 | 3<br>3.7 |    |
| Zero gate voltage collector current<br>$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$<br>$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$ | $I_{CES}$     | -<br>- | 1.5<br>6   | 2<br>-   | mA |
| Gate-emitter leakage current<br>$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$                                                                                                    | $I_{GES}$     | -      | -          | 200      |    |

#### AC Characteristics

|                                                                                               |           |    |     |   |    |
|-----------------------------------------------------------------------------------------------|-----------|----|-----|---|----|
| Transconductance<br>$V_{CE} = 20\text{ V}, I_C = 100\text{ A}$                                | $g_{fs}$  | 54 | -   | - | S  |
| Input capacitance<br>$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$            | $C_{iss}$ | -  | 6.5 | - | nF |
| Output capacitance<br>$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$           | $C_{oss}$ | -  | 1   | - |    |
| Reverse transfer capacitance<br>$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | $C_{rss}$ | -  | 0.5 | - |    |

### Electrical Characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

| Parameter | Symbol | Values |      |      | Unit |
|-----------|--------|--------|------|------|------|
|           |        | min.   | typ. | max. |      |

### Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

|                                                                                                                                   |              |   |     |     |    |
|-----------------------------------------------------------------------------------------------------------------------------------|--------------|---|-----|-----|----|
| Turn-on delay time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 100\text{ A}$<br>$R_{Gon} = 6.8\text{ }\Omega$    | $t_{d(on)}$  | - | 130 | 260 | ns |
| Rise time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 100\text{ A}$<br>$R_{Gon} = 6.8\text{ }\Omega$             | $t_r$        | - | 80  | 160 |    |
| Turn-off delay time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = -15\text{ V}$ , $I_C = 100\text{ A}$<br>$R_{Goff} = 6.8\text{ }\Omega$ | $t_{d(off)}$ | - | 400 | 600 |    |
| Fall time<br>$V_{CC} = 600\text{ V}$ , $V_{GE} = -15\text{ V}$ , $I_C = 100\text{ A}$<br>$R_{Goff} = 6.8\text{ }\Omega$           | $t_f$        | - | 70  | 100 |    |

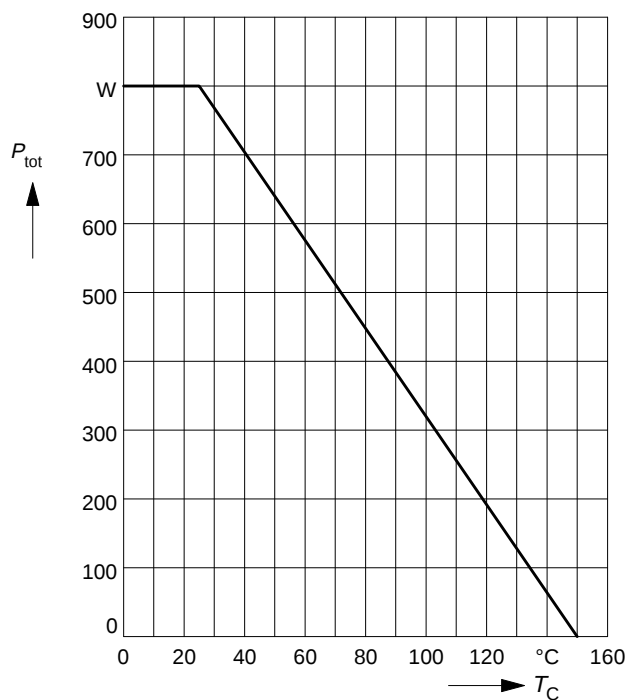
### Free-Wheel Diode

|                                                                                                                                                                                            |          |   |            |          |               |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------|---|------------|----------|---------------|
| Diode forward voltage<br>$I_F = 100\text{ A}$ , $V_{GE} = 0\text{ V}$ , $T_j = 25\text{ °C}$<br>$I_F = 100\text{ A}$ , $V_{GE} = 0\text{ V}$ , $T_j = 125\text{ °C}$                       | $V_F$    | - | 2.3<br>1.8 | 2.8<br>- | V             |
| Reverse recovery time<br>$I_F = 100\text{ A}$ , $V_R = -600\text{ V}$ , $V_{GE} = 0\text{ V}$<br>$dI_F/dt = -1000\text{ A}/\mu\text{s}$ , $T_j = 25\text{ °C}$                             | $t_{rr}$ | - | 0.3        | -        |               |
| Reverse recovery charge<br>$I_F = 100\text{ A}$ , $V_R = -600\text{ V}$ , $V_{GE} = 0\text{ V}$<br>$dI_F/dt = -1000\text{ A}/\mu\text{s}$<br>$T_j = 25\text{ °C}$<br>$T_j = 125\text{ °C}$ | $Q_{rr}$ | - | 4<br>12    | -<br>-   | $\mu\text{C}$ |
|                                                                                                                                                                                            |          | - |            |          |               |

## Power dissipation

$$P_{\text{tot}} = f(T_C)$$

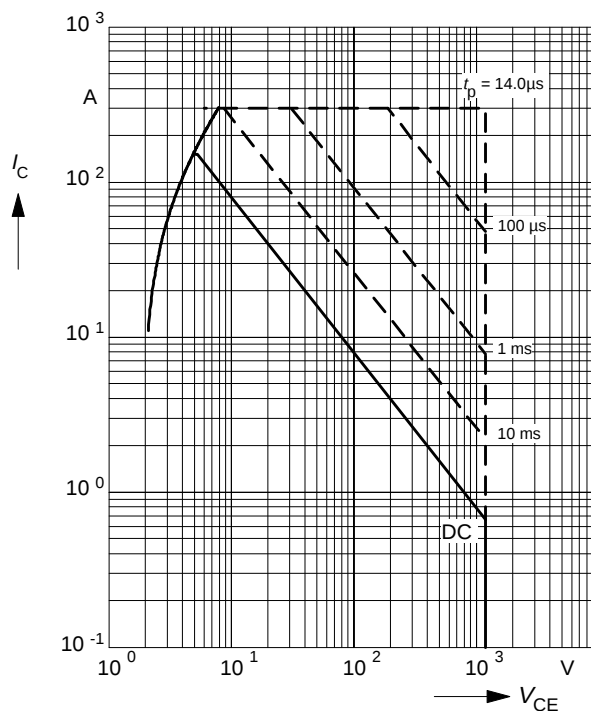
parameter:  $T_j \leq 150^\circ\text{C}$



## Safe operating area

$$I_C = f(V_{CE})$$

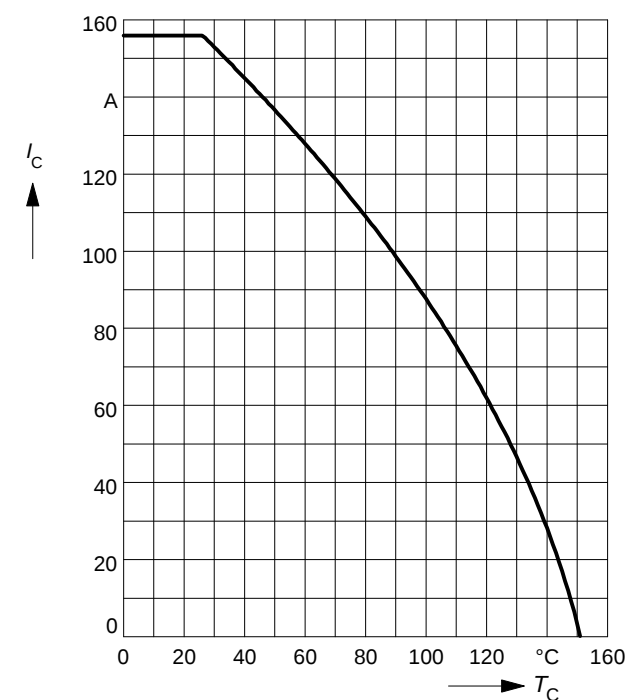
parameter:  $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$



## Collector current

$$I_C = f(T_C)$$

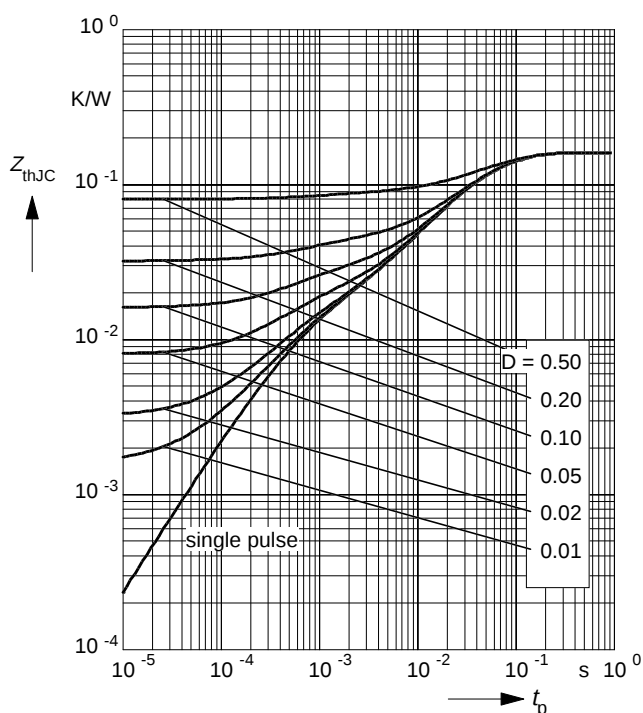
parameter:  $V_{GE} \geq 15\text{ V}$ ,  $T_j \leq 150^\circ\text{C}$



## Transient thermal impedance IGBT

$$Z_{\text{thJC}} = f(t_p)$$

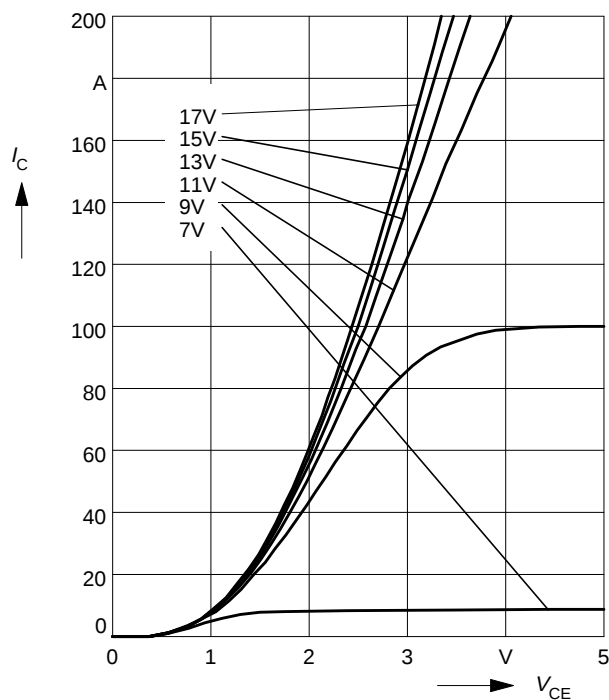
parameter:  $D = t_p / T$



## Typ. output characteristics

$$I_C = f(V_{CE})$$

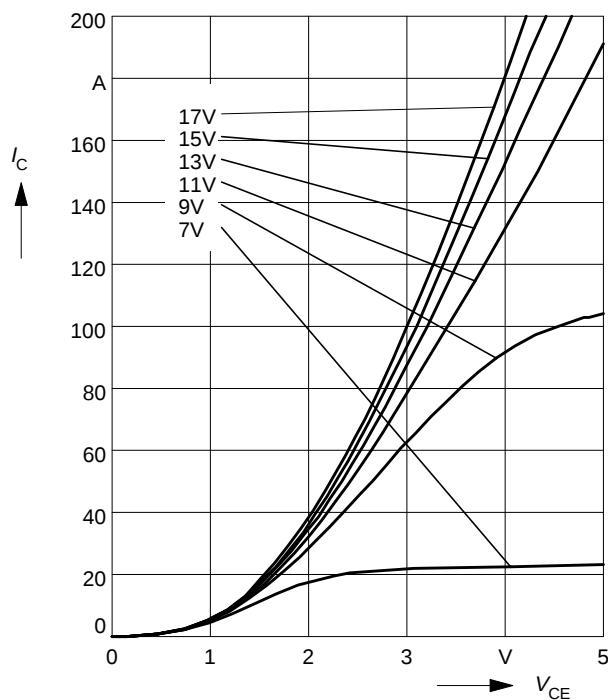
parameter:  $t_p = 80 \mu s$ ,  $T_j = 25^\circ C$



## Typ. output characteristics

$$I_C = f(V_{CE})$$

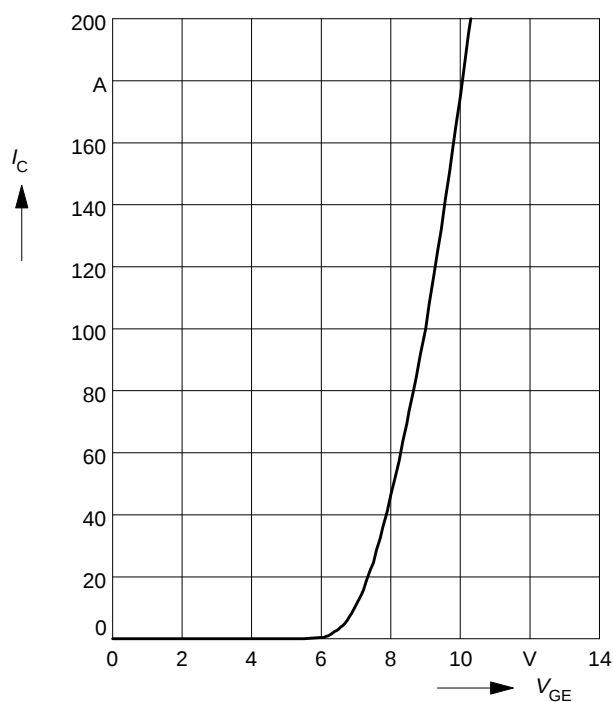
parameter:  $t_p = 80 \mu s$ ,  $T_j = 125^\circ C$



## Typ. transfer characteristics

$$I_C = f(V_{GE})$$

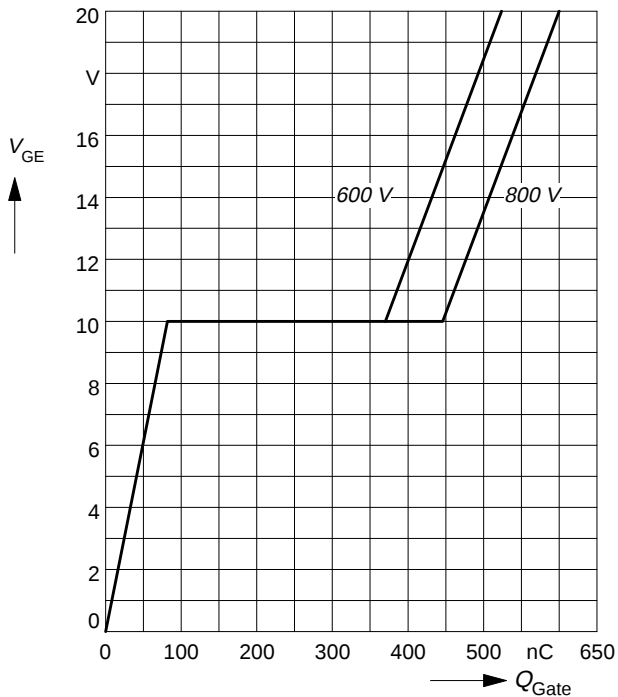
parameter:  $t_p = 80 \mu s$ ,  $V_{CE} = 20 V$



### Typ. gate charge

$$V_{GE} = f(Q_{Gate})$$

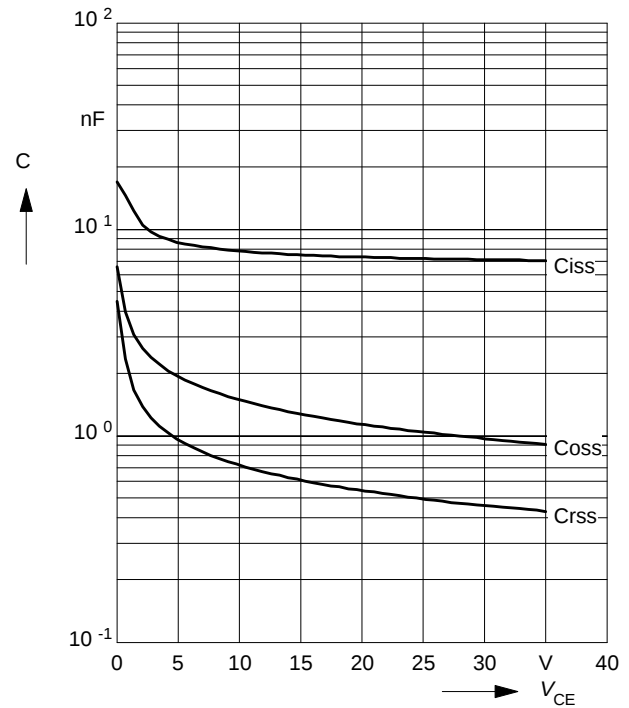
parameter:  $I_{C\ puls} = 100\ A$



### Typ. capacitances

$$C = f(V_{CE})$$

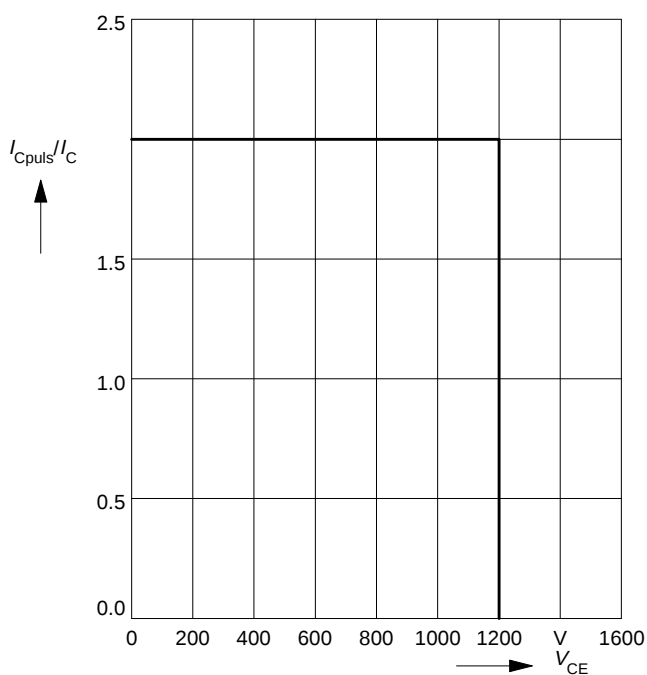
parameter:  $V_{GE} = 0\ V$ ,  $f = 1\ MHz$



### Reverse biased safe operating area

$$I_{C\ puls} = f(V_{CE}), T_j = 150^\circ C$$

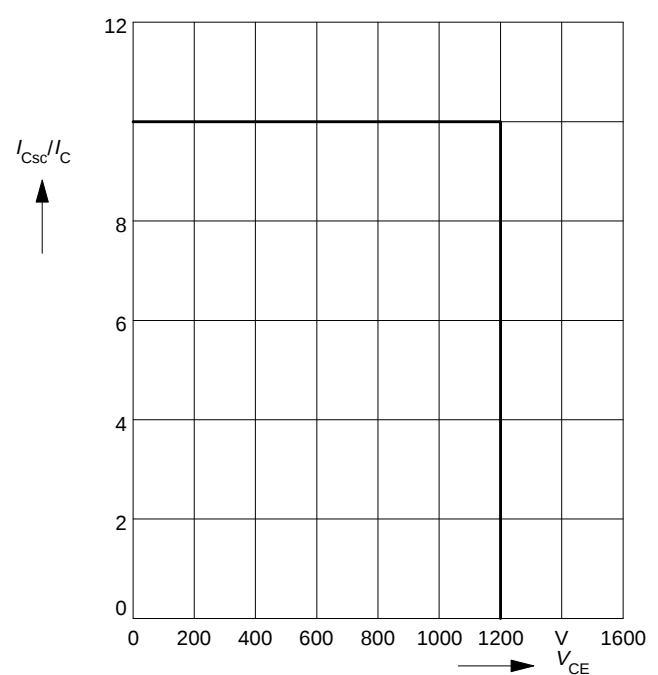
parameter:  $V_{GE} = 15\ V$



### Short circuit safe operating area

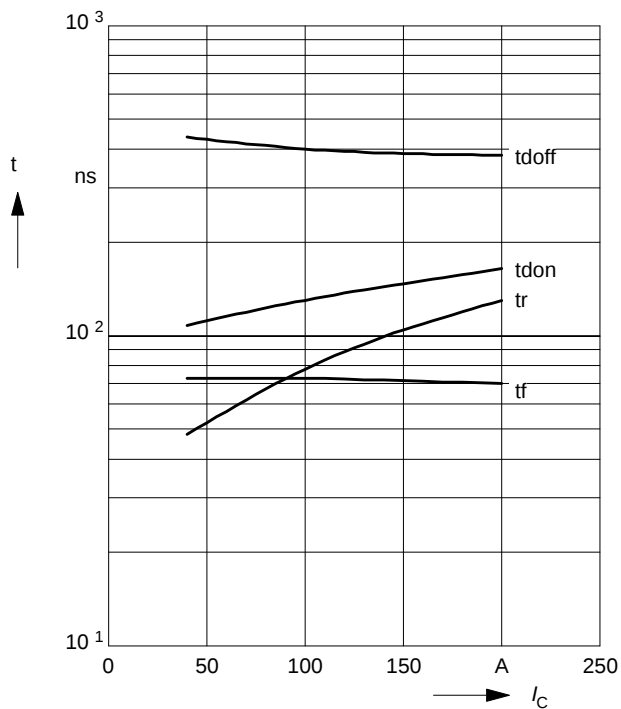
$$I_{C\ sc} = f(V_{CE}), T_j = 150^\circ C$$

parameter:  $V_{GE} = \pm 15\ V$ ,  $t_{SC} \leq 10\ \mu s$ ,  $L < 25\ nH$



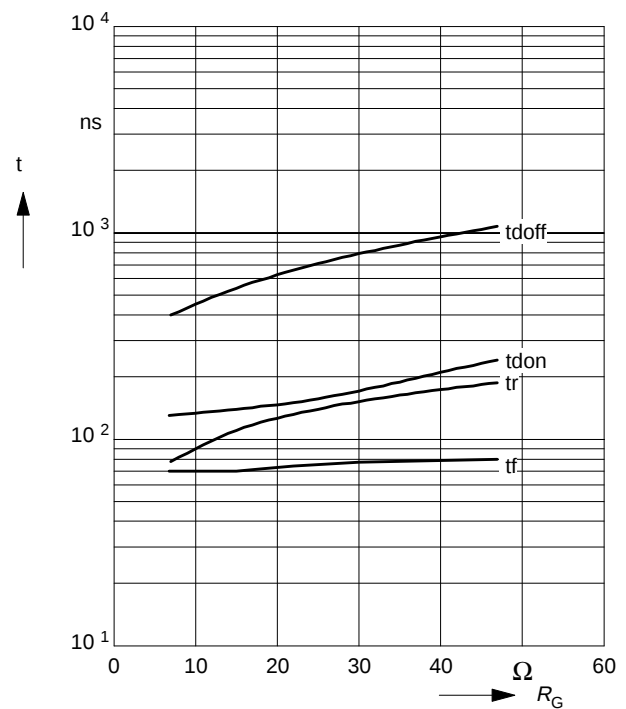
## Typ. switching time

$I = f(I_C)$ , inductive load,  $T_j = 125^\circ\text{C}$   
 par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $R_G = 6.8\ \Omega$



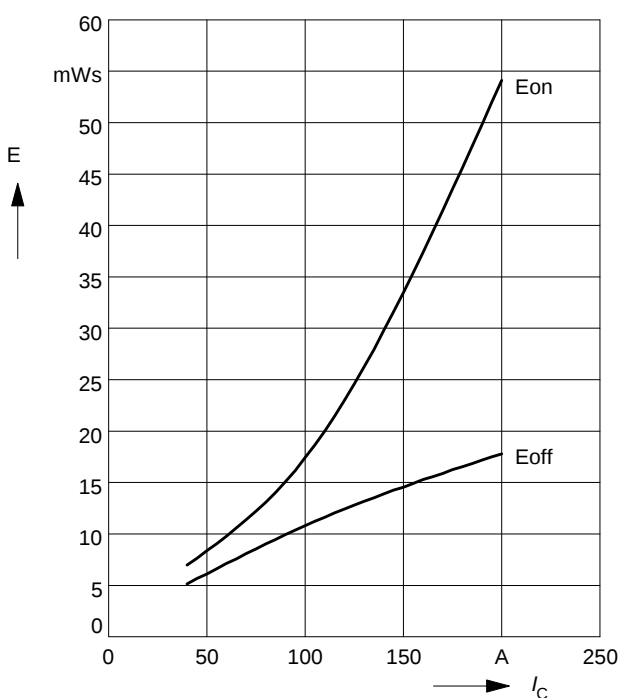
## Typ. switching time

$t = f(R_G)$ , inductive load,  $T_j = 125^\circ\text{C}$   
 par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 100\text{ A}$



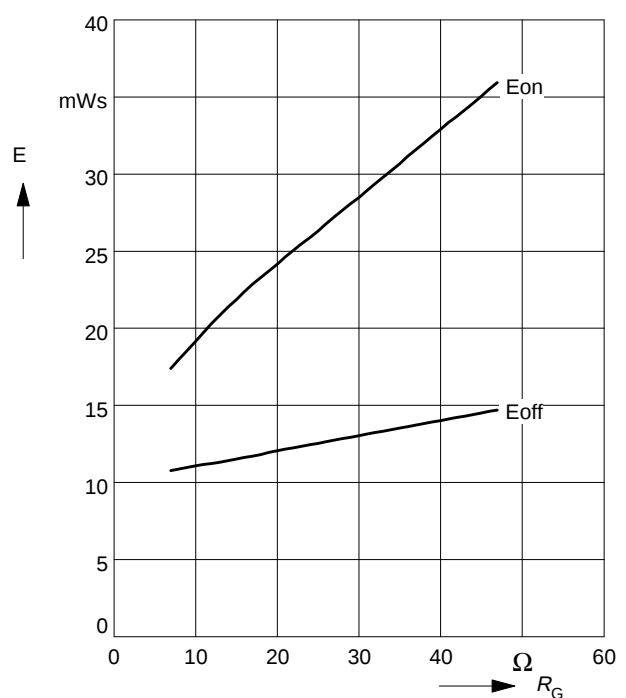
## Typ. switching losses

$E = f(I_C)$ , inductive load,  $T_j = 125^\circ\text{C}$   
 par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $R_G = 6.8\ \Omega$



## Typ. switching losses

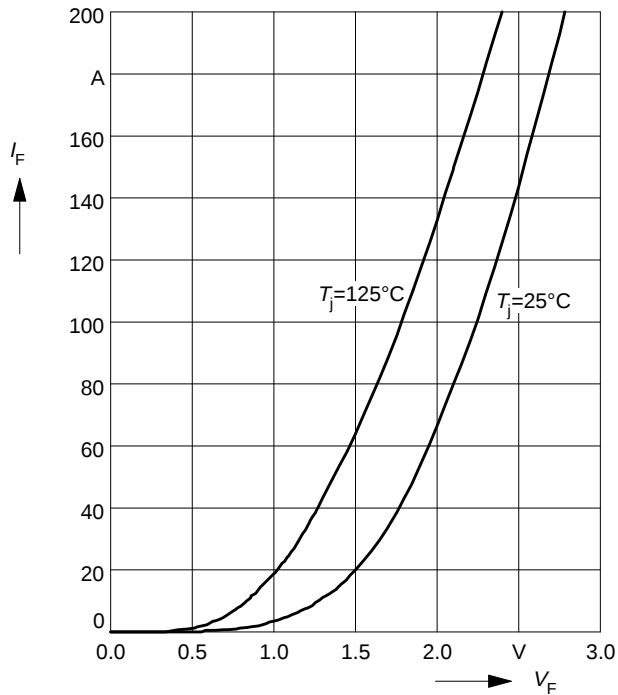
$E = f(R_G)$ , inductive load,  $T_j = 125^\circ\text{C}$   
 par.:  $V_{CE} = 600\text{ V}$ ,  $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 100\text{ A}$



### Forward characteristics of fast recovery reverse diode

$$I_F = f(V_F)$$

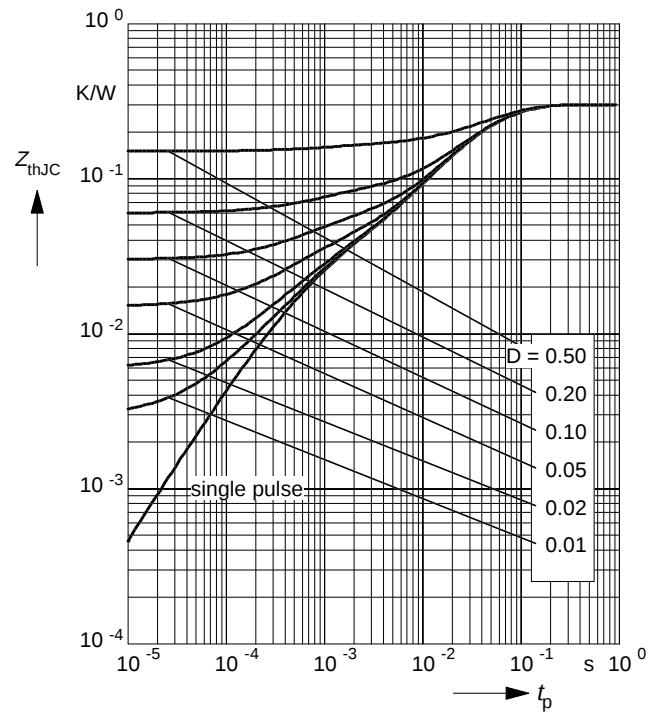
parameter:  $T_j$



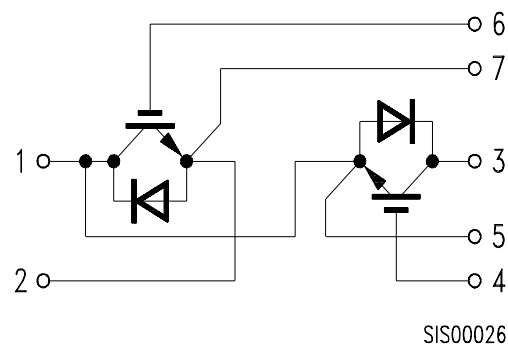
### Transient thermal impedance Diode

$$Z_{thJC} = f(t_p)$$

parameter:  $D = t_p / T$



Circuit Diagram



Package Outlines

Dimensions in mm

Weight: 420 g

